

# Noise Figure vs. PM noise Measurements: A study at Microwave Frequencies

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- Noise Figure of an amplifier from PM noise measurement
- Thermal noise level in the presence of carrier (referenced to 0dBm )
  - 177dBc/Hz
  - or
  - 174dBc/Hz

# Noise Figure of an amplifier

- Noise figure:

It is a measure of degradation in the signal-to-noise ratio between input and output of an amplifier

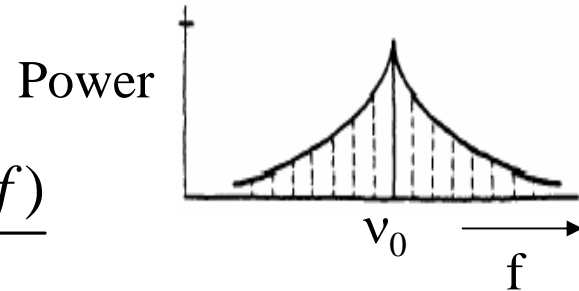
$$\text{NF} = \frac{(S_i/N_i)}{(S_o/N_o)}$$

- NF of a noiseless amplifier = 1 (0dB)
- NF of a noisy amplifier > 1 (0dB)
- Meaningful only at offset frequencies where phase noise is white

# Derivation of noise figure from PM noise measurement in the presence of carrier

RF spectrum can be written as

$$S_{\text{RF}}(f) = \frac{\text{PSD}V_N(v_0 - f) + \text{PSD}V_N(v_0 + f)}{V_0^2}$$



$V_0$  = rms voltage level of the carrier

$\text{PSD}V_N(v_0 \pm f)$  = power spectral density of the voltage noise

$v_0$  = carrier frequency

$f$  = the offset or Fourier frequency

- **Random RF noise is divided equally between AM noise and PM noise**

⇒ PSD of PM noise,  $S_{\phi}(f) = (1/2)S_{\text{RF}}(f)$

- **Single sideband phase noise (by convention only)**

$$\Lambda(f) = (1/2)S_{\phi}(f) = (1/4)S_{\text{RF}}(f)$$

$$\Rightarrow L(f)_{\text{rad}} = \frac{\text{PSD}V_N(\nu_0 - f) + \text{PSD}V_N(\nu_0 + f)}{(4)V_0^2}$$

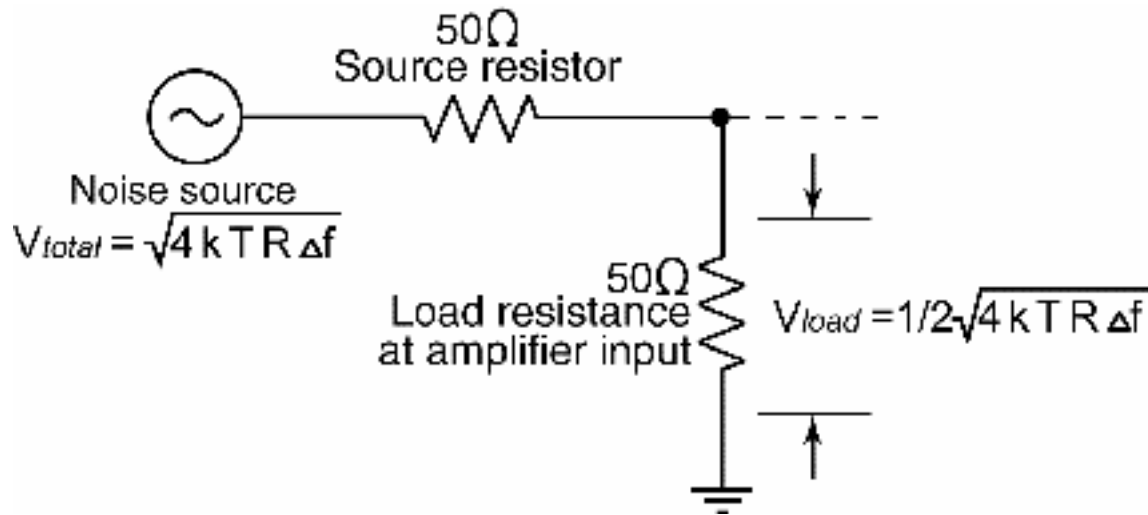


Fig: Equivalent input circuit showing the thermal noise generator with a source resistance and terminated into the amplifier input resistance

$$L(f)_{rad} = \frac{kTR}{2V_0^2} = \frac{kT}{2P_i} \quad (\Delta f = 1)$$

$$T=290^0 \text{ K}, k = 1.38 \times 10^{-23} \text{ J/K}$$

$$A(f) = 10\log(A(f)_{rad}) = -177\text{dBc/Hz} \quad (\text{Referenced to 0dBm})$$

## Wideband PM noise floor of an amplifier

- Output of amplifier

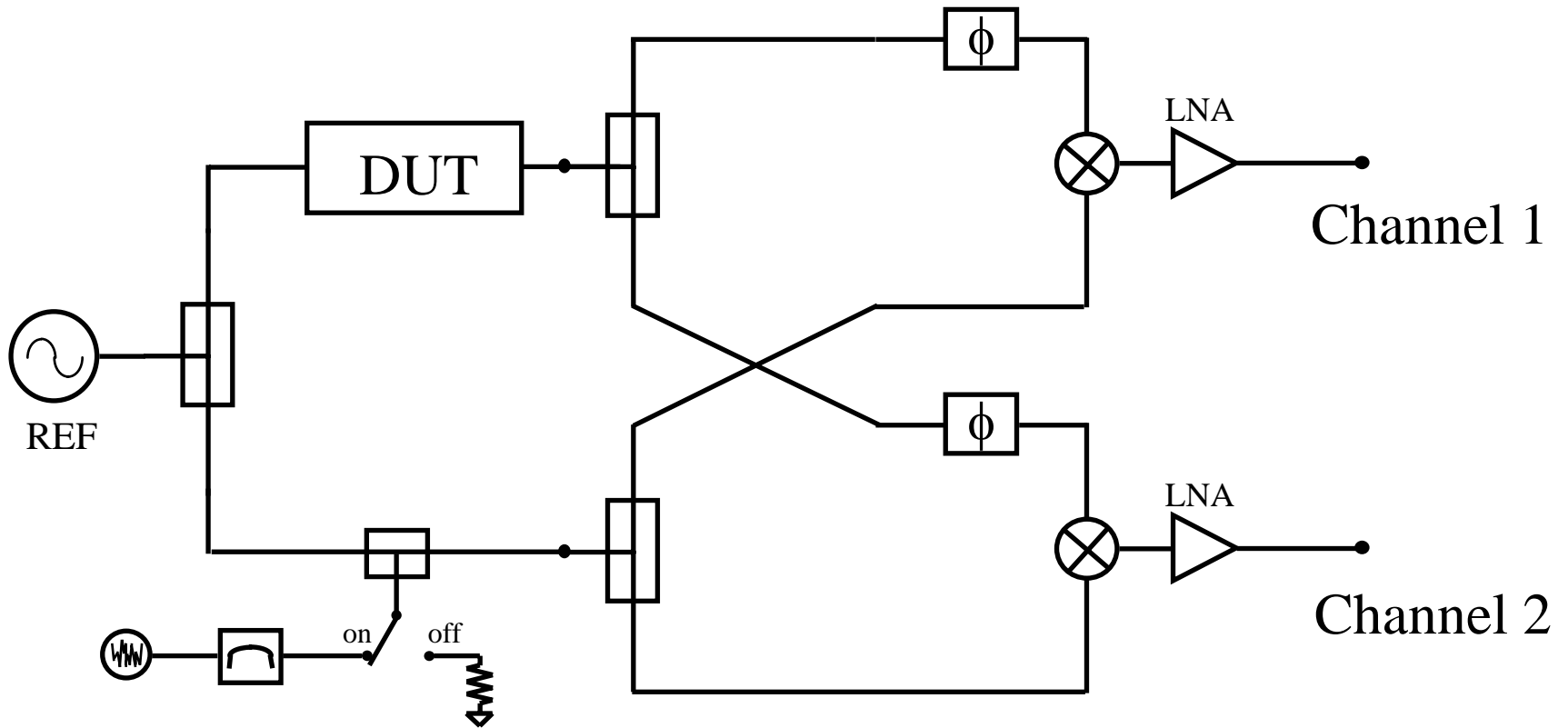
$$L(f)_{rad} = \frac{kTGNF}{2P_o} = \frac{kTNF}{2P_i}$$

- In terms of dBc/Hz wideband noise floor of the amplifier

$$A(f) = -177 - P_i + NF$$

$$NF = 177 + P_i + A(f)$$

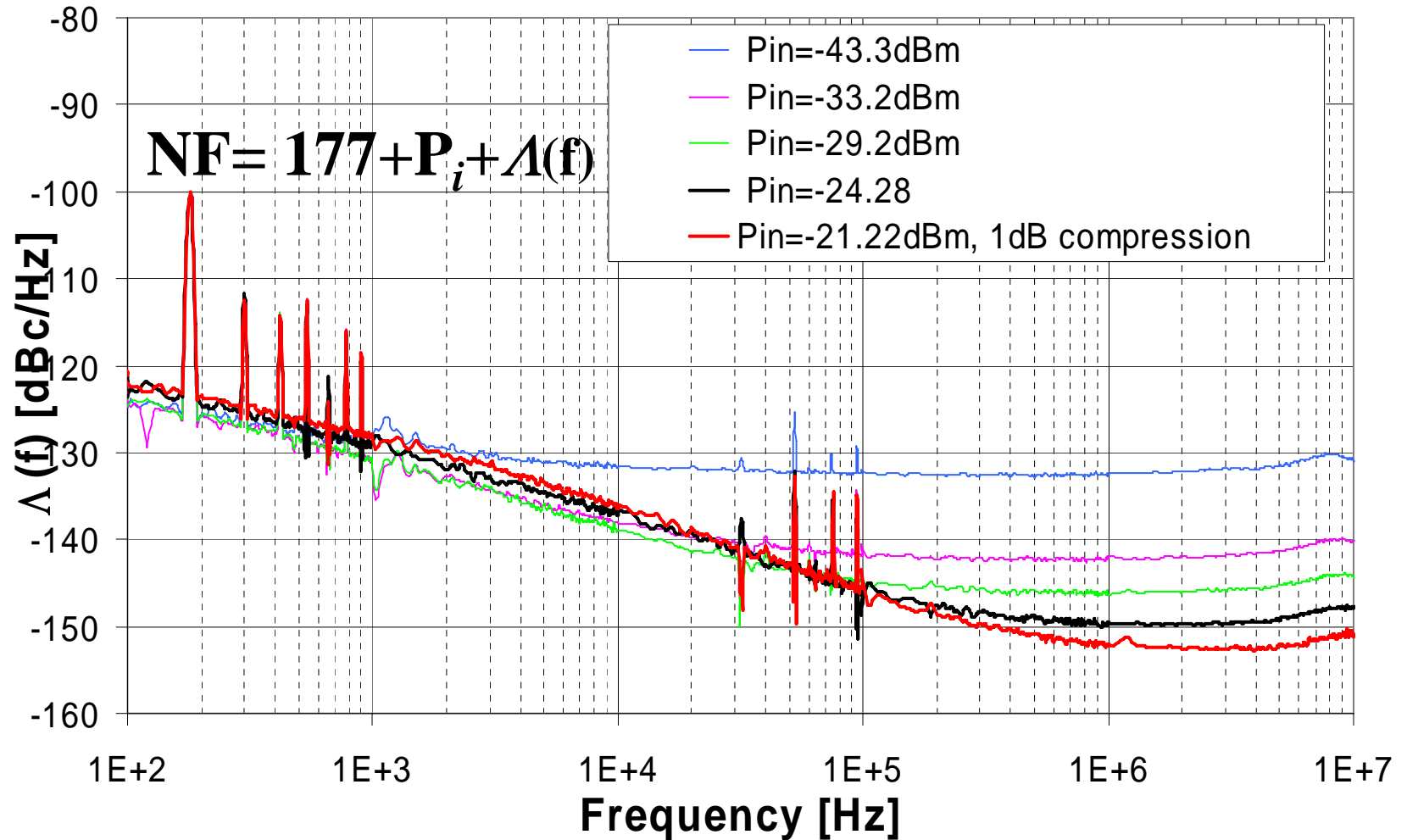
# Two channel cross-correlation system for measuring PM noise of amplifier



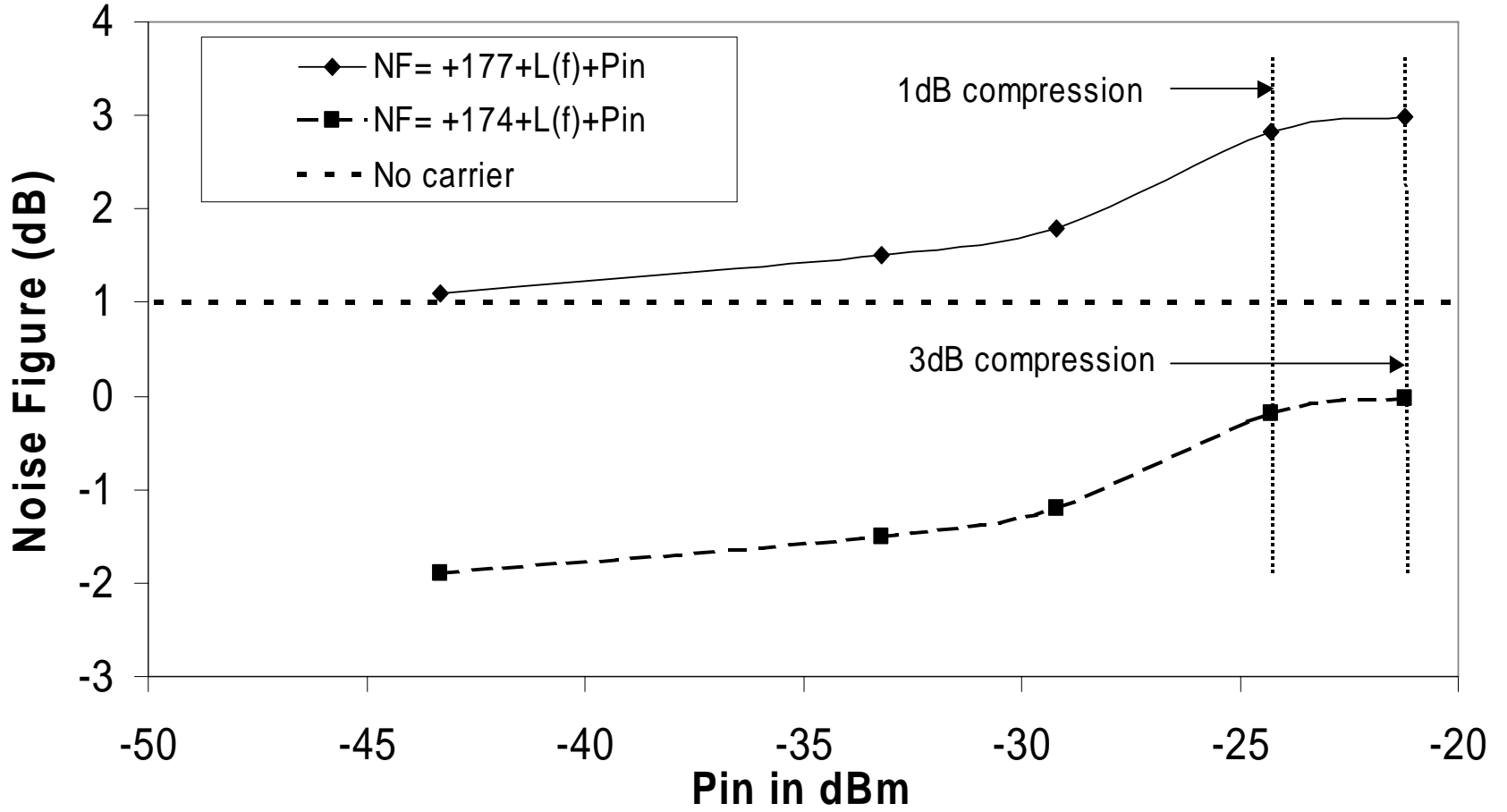
# Phase Noise of GaAs HEMFET Amplifier

Gain=32.5dB, NF=1dB

Frequency = 10GHz

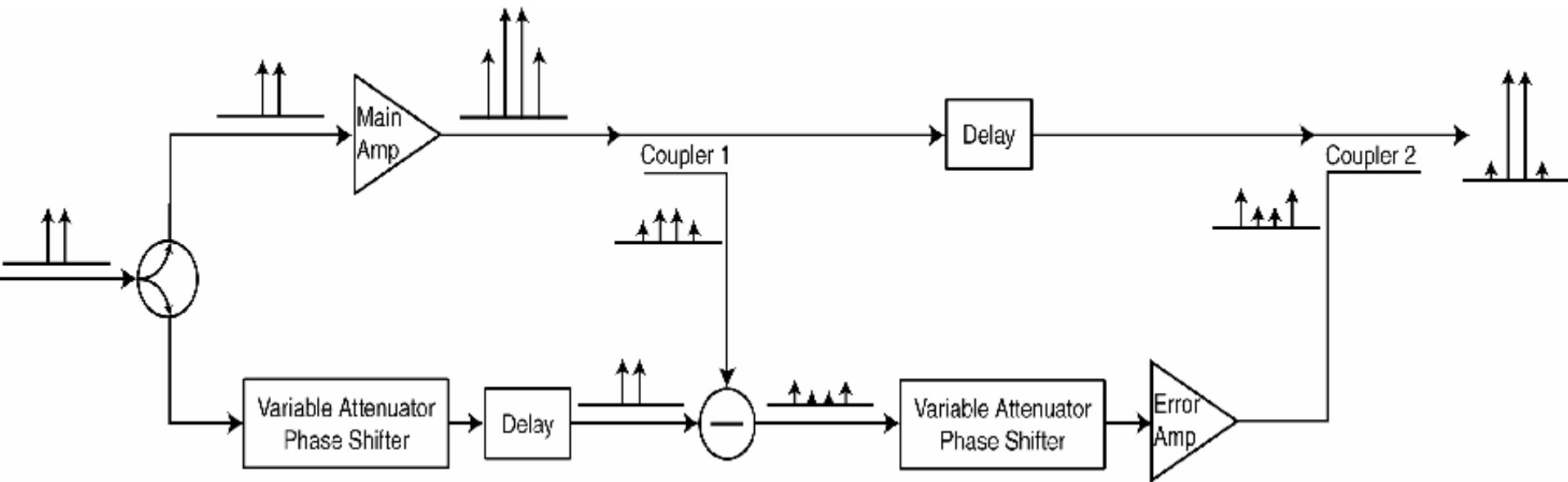


# Input power vs NF



An example of an amplifier  
whose NF is not a function of  
carrier power

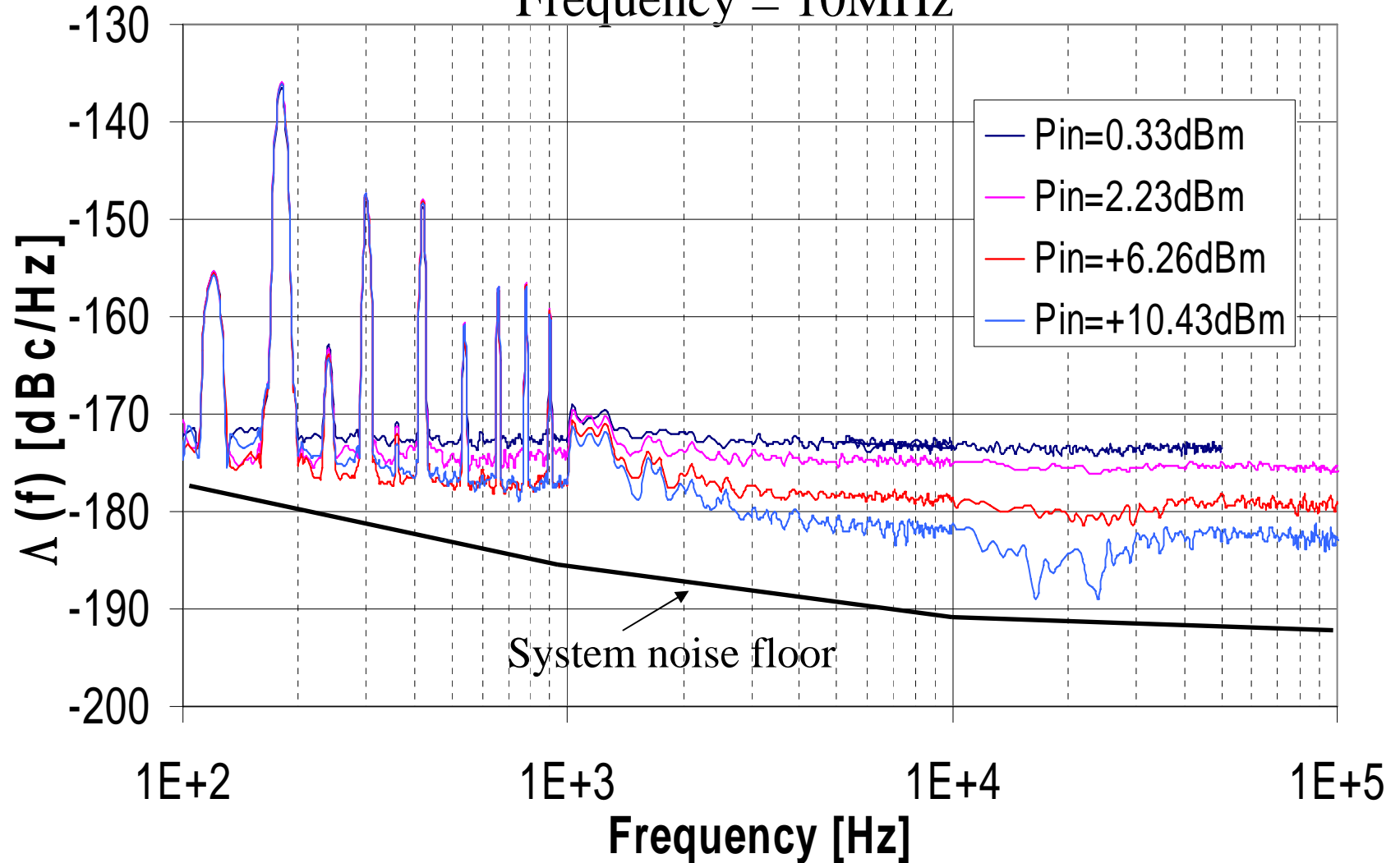
# Simplified block diagram of feed-forward amplifier configuration



# PM noise of Feed-forward amplifier

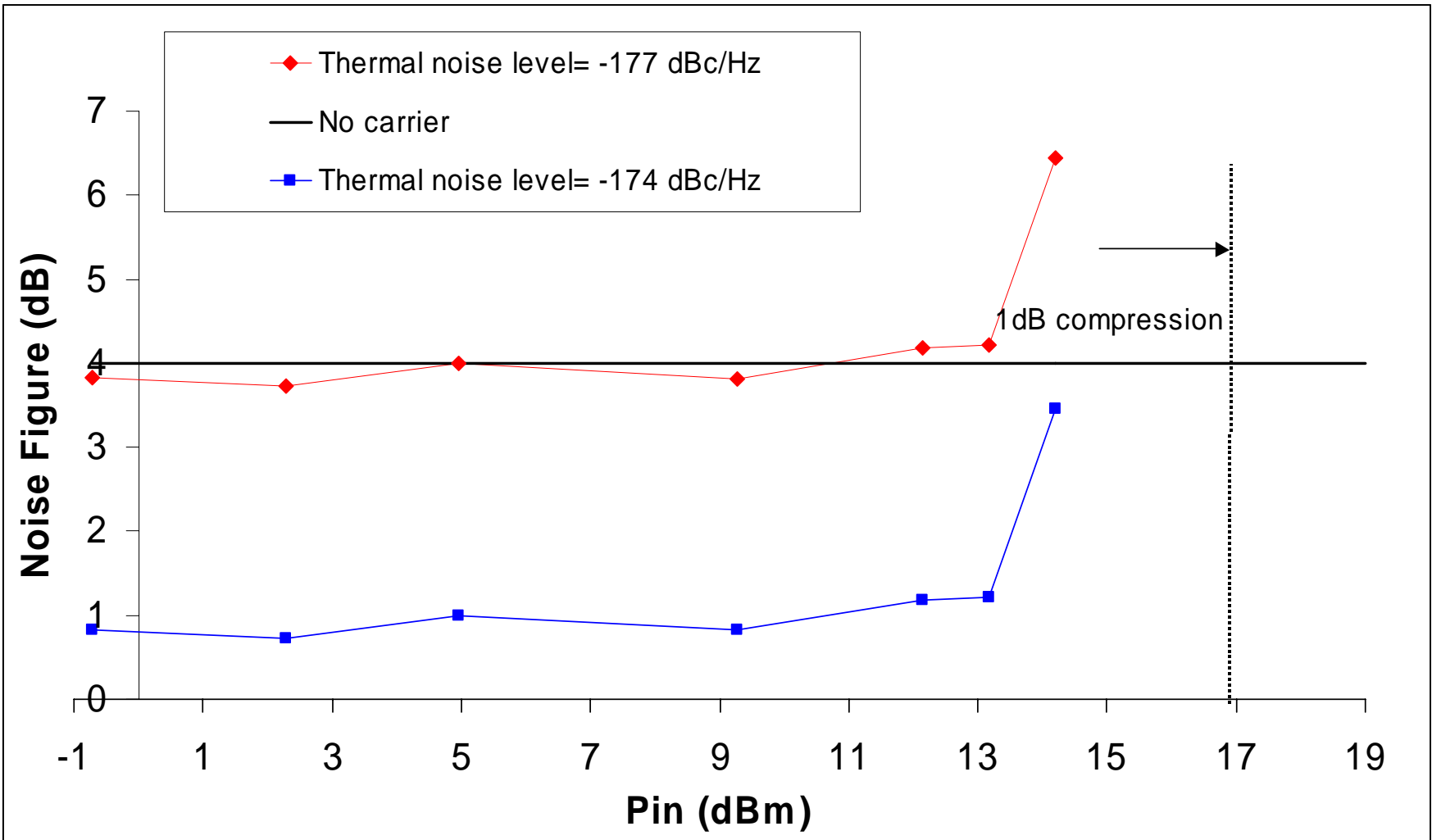
Gain= 12.5dB, Pout=23dBm, NF=4dB

Frequency = 10MHz

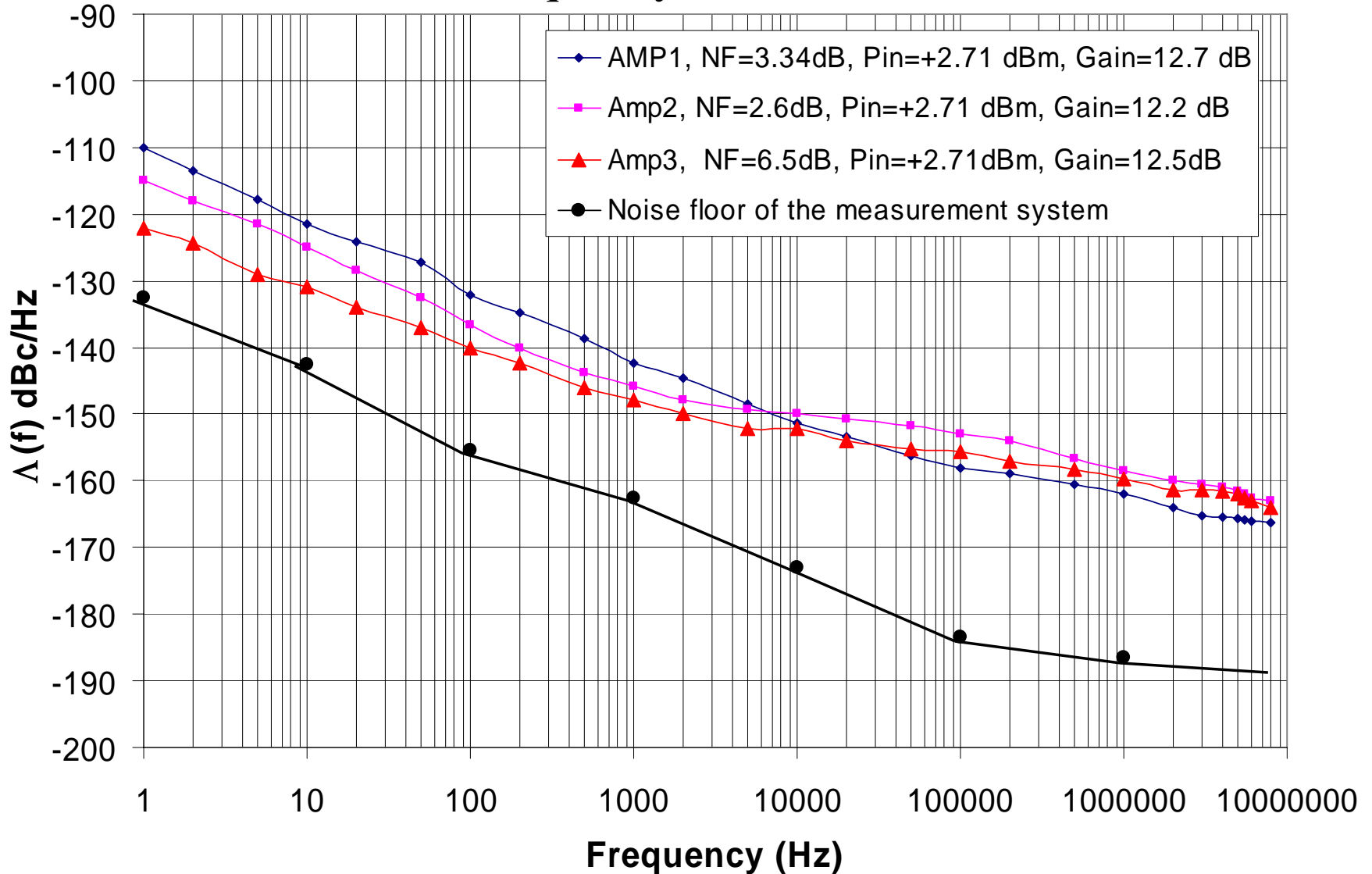


# Noise figure of Feed-forward amplifier

Frequency = 10MHz, Gain= 12.5dB, Pout=+27dBm,  
NF=4dB



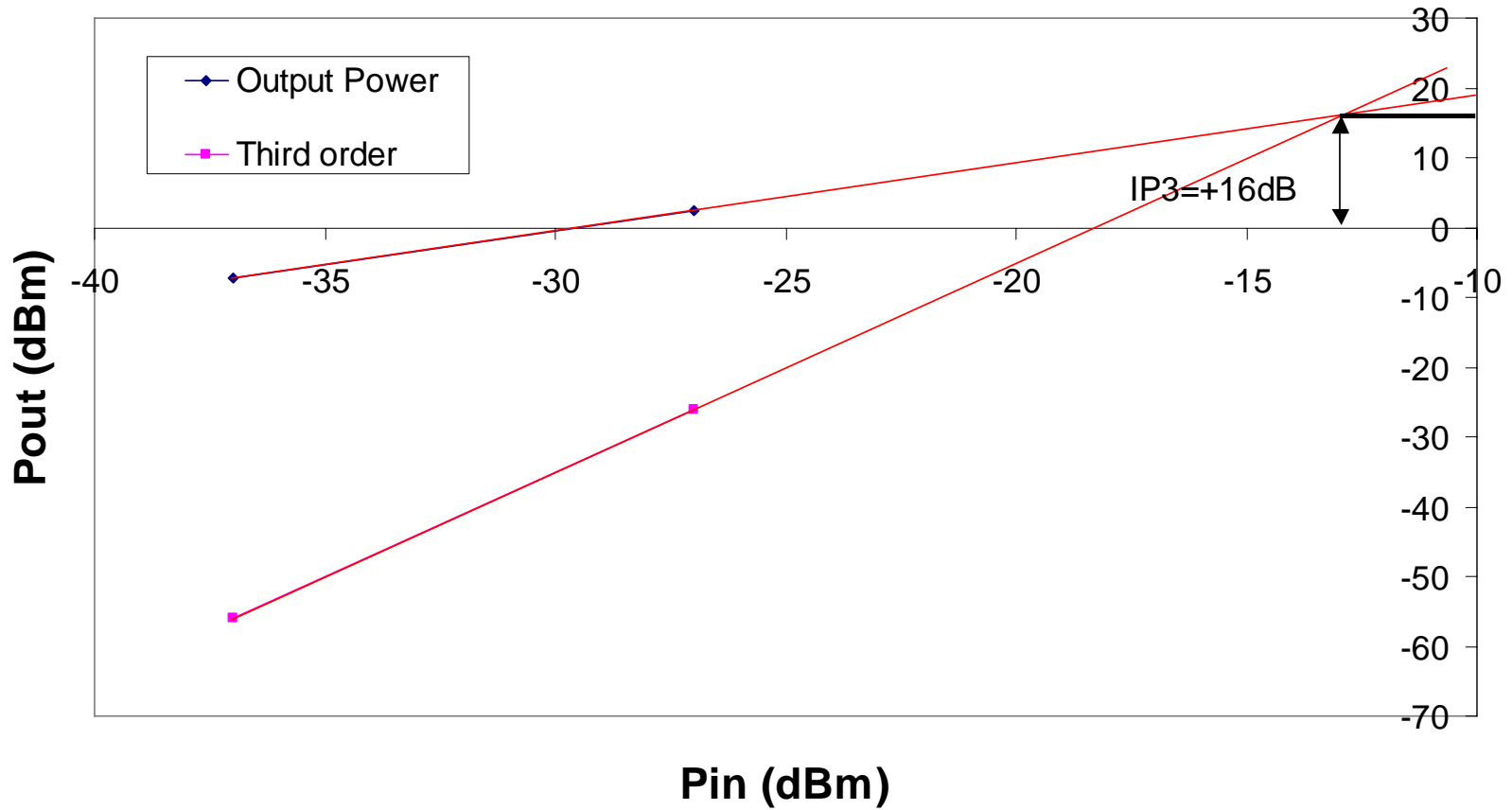
# 1/f noise of different amplifiers having different NF Frequency = 10GHz



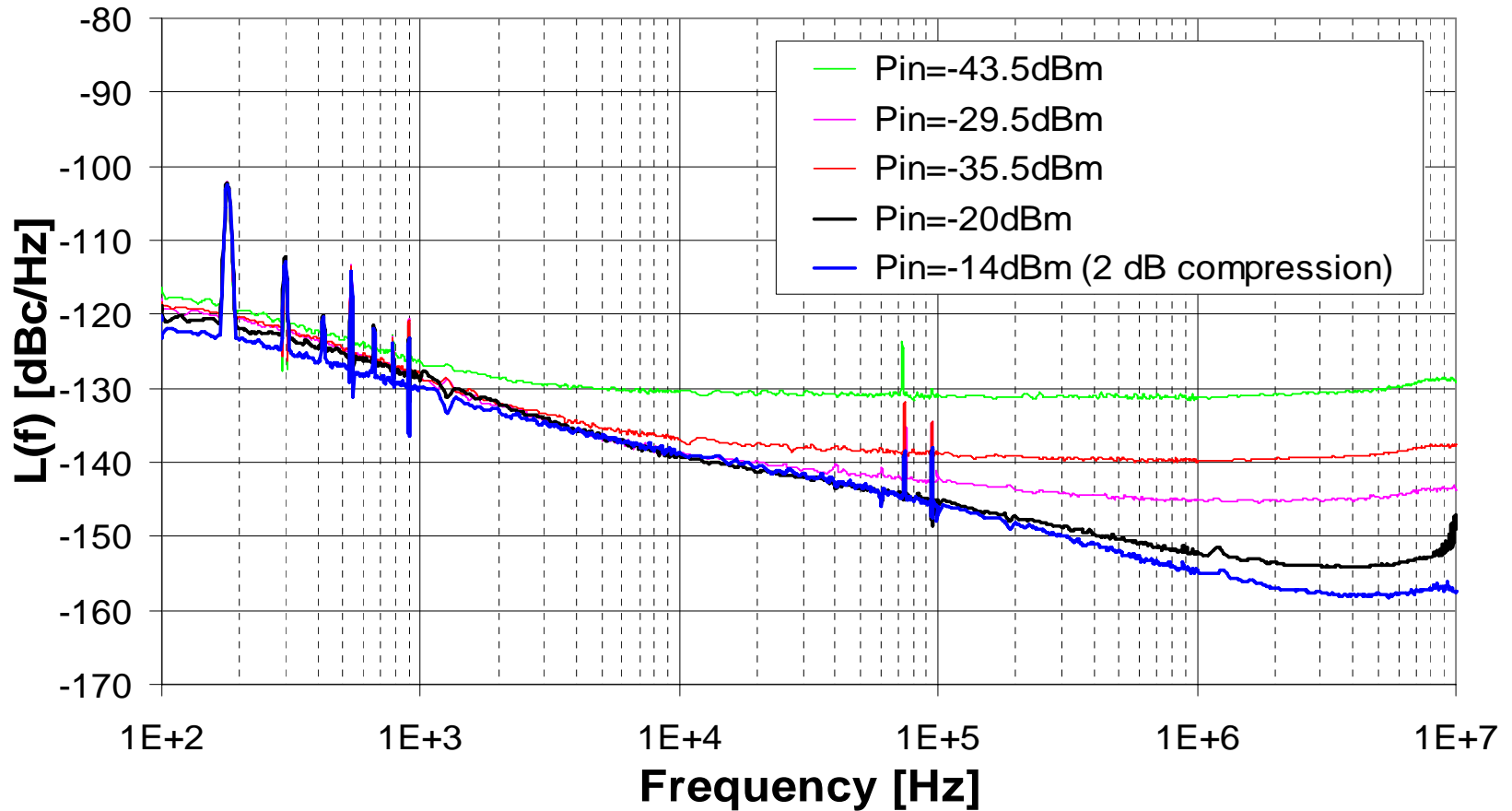
## Conclusion

- Merit of an amplifier is better characterized by PM noise measurement than NF measurement with no carrier
- NF of a non-linear amplifier is a function of carrier power due to non-linear inter modulation process whereas for linear amplifier NF is independent of carrier power
- In the presence of carrier, thermal noise level is  $-177\text{dBc/Hz}$  referenced to  $0\text{dBm}$

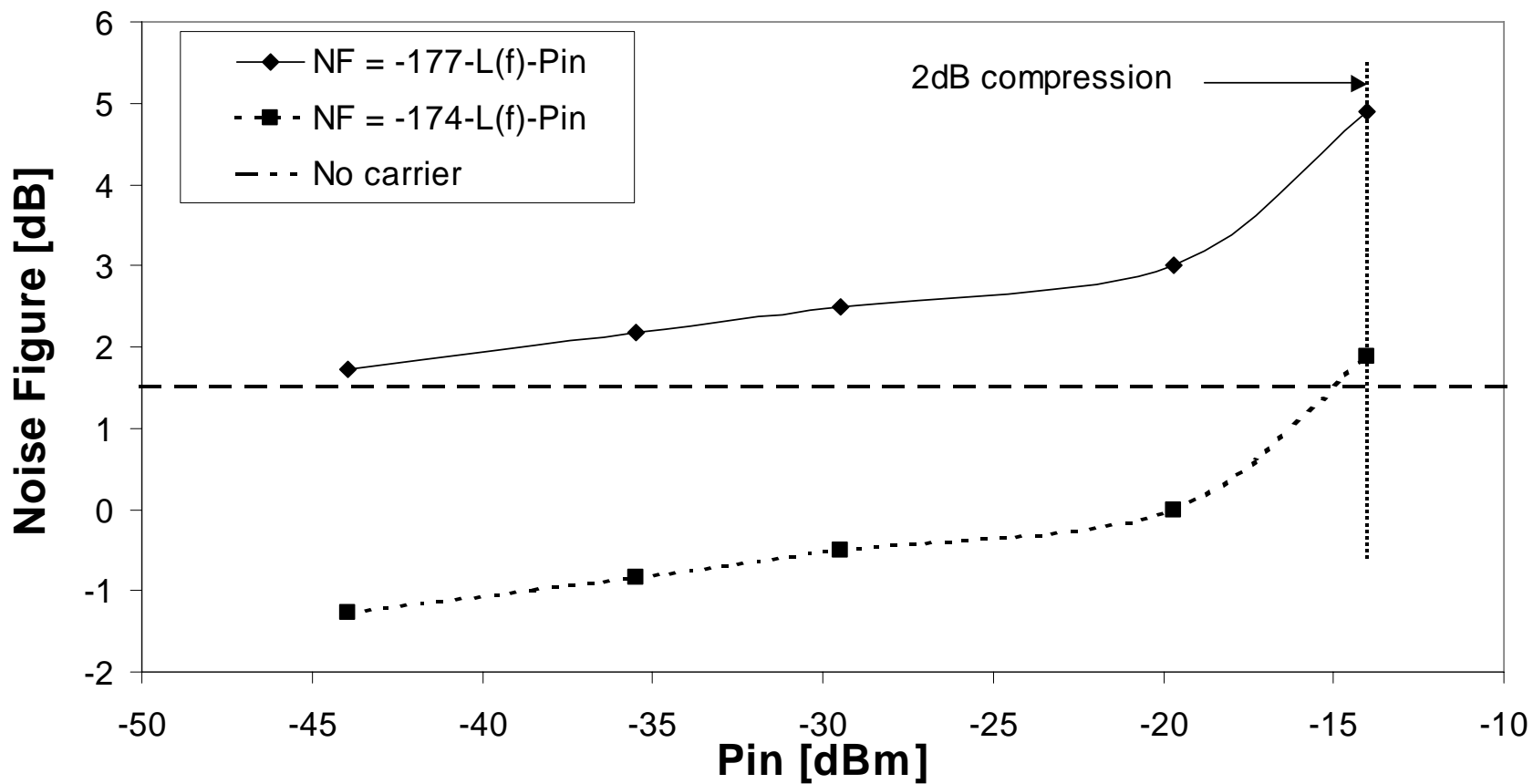
# Third order inter-modulation product IP3



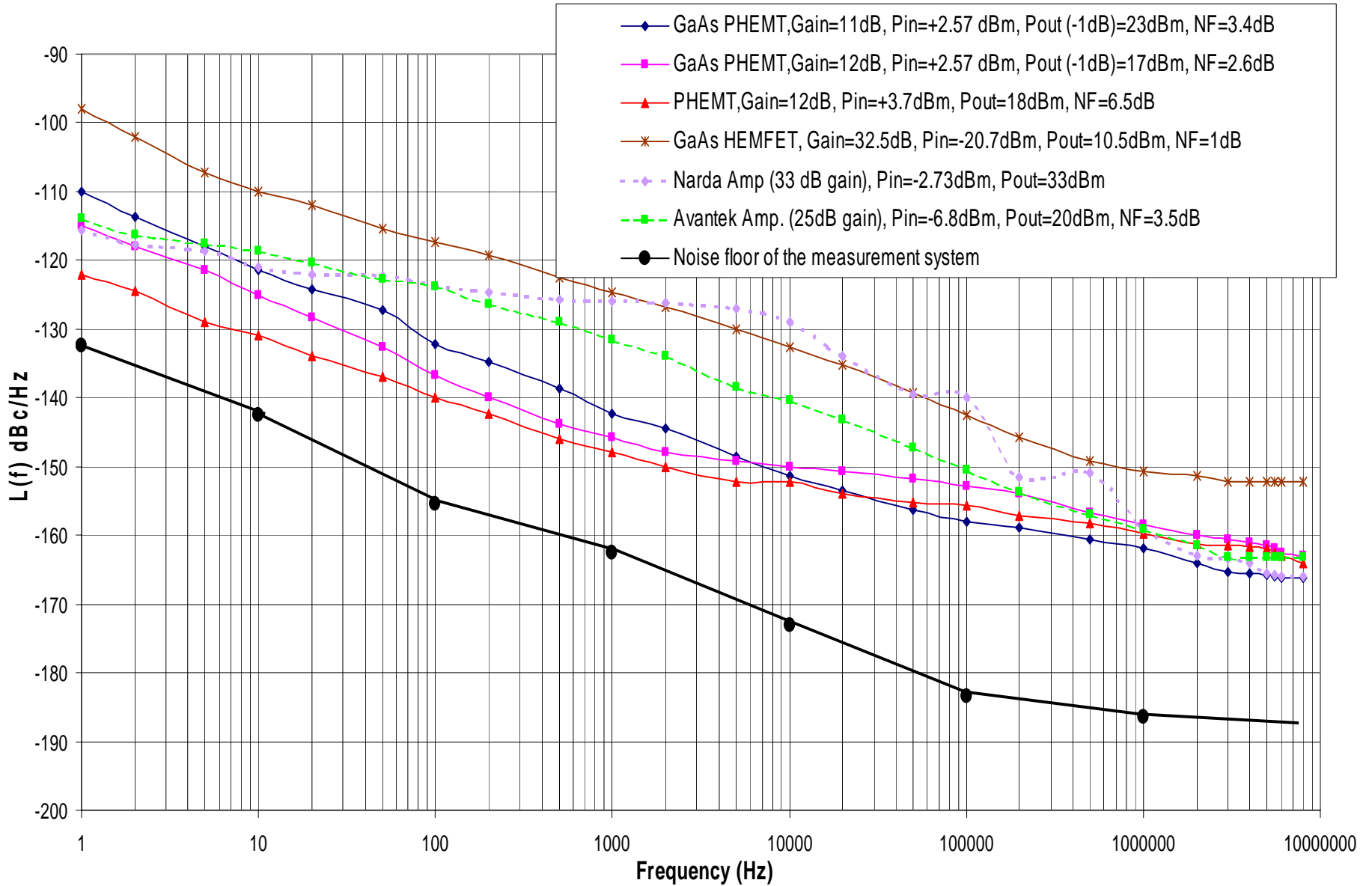
# Phase Noise of GaAs FET amplifier, NF= 1.5, Gain=35dB Frequency=10GHz



# Input power vs NF



### Phase noise of different amplifiers at 10GHz



## Confidence Interval

$$\begin{aligned} S_{\phi}^m(f) &= S_{\phi}^s(f) \left[ 1 \pm \frac{k}{\sqrt{N}} \right] \\ &= S_{\phi}^s(f) [1 \pm 0.00038] \end{aligned}$$

$m$  = cross-correlated noise

$s$  = single channel noise

$N$  = number of samples = 5000

$K$  = confidence interval index = 1.9